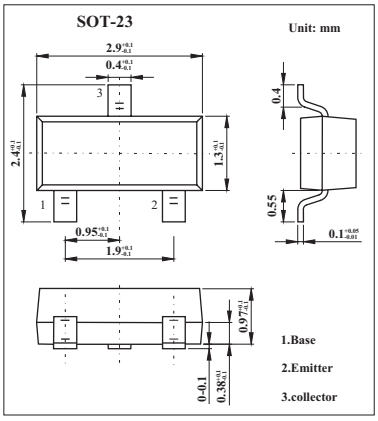
Silicon NPN Epitaxial

2SC4702



■ Features

- High breakdown voltage

  V_{CEO} = 300 V

- Small Cob

  C_{ob} = 1.5 pF Typ.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V
Collector cutoff current	I_{CBO}	V_{CB} = 250V, I_E=0			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 30mA , I_B = 3mA			0.5	V
DC current gain	h_{FE}	V_{CE} = 6V , I_C = 2mA	60		150	
Gain bandwidth product	f_T	V_{CE} = 6V , I_C = 5mA		80		MHz
Collector output capacitance	Cob	V_{CB} = 10V , I_E=0, f = 1MHz		1.5		pF

■ Marking

Marking	XV-